

Electronics Materials Information

Critical Materials Report Advisory: QUARTERLY UPDATE for The Critical Materials Council for Semiconductor Fabricators (CMCFabs)

By TECHCET Group A TECHCET CA LLC Company March 2016 www.Techcet.com

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Electronics Materials Information

Section 1 QUARTERLY UPDATE ALD/CVD High K and Metal Precursors Sematech Critical Materials Council

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ALD/CVD Industry Outlook

DEPOSITION SYSTEMS Wafer Equipment Market (Billion US\$) (WW Sales in \$M) 5000 VLSI Research April 2016 CVD Tools Diffusion/Furnace CVD **PVD** Tools ALD Tools Other Wafer Assembly, 3.30 Test, 3.60 4000 RTP Tools Electro Plating Tools Processes, 2.20 Process 3000 Lithography, Diagnostics, _ 8.10 3.90 ALD Deposition, 2000 Etch & Clean, 8.00 8.10 1000 Adopted from ASMI INVESTOR PRESENTATION 0 2015 2017 2014 2016 2018 2019 2020 July 28, 2016, Q2 2016 RESULTS Risto Puhakka VLSI Research May 2016, CMC Conference Hillsboro

CVD & ALD show continued high growth Potential

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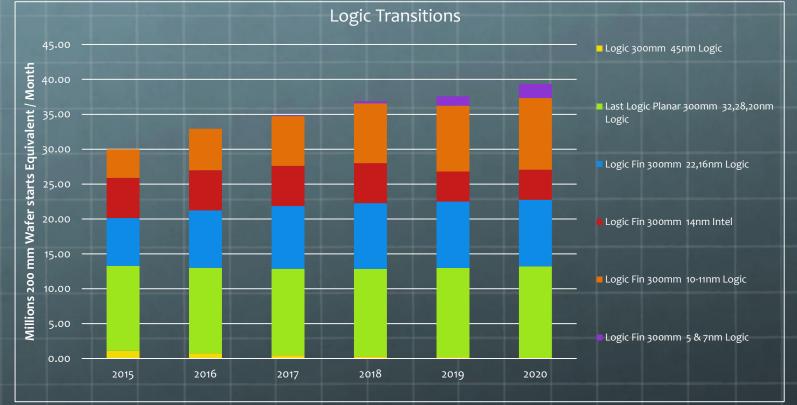
- Growth driven by scaled 3D devices (FinFET & 3DNAND) and Wafer starts
- ALD passed PVD in 2015(!)

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ALD/CVD Industry Outlook



- Intel 45 nm and all sub 45 nm nodes except for 32/28 Low power use ALD
- Growth in Wafer Starts & Transition to 10 & 7 nm will drive growth in ALD &
 CVD Metal precursors further especially Hf High-k & Cobalt (see slide 11)

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Scaling trend \rightarrow ALD Migration

I - Migration to ALD due to shrink

- LPCVD SiN and SiO2
- PECVD SiN and SiO2
- CVD Metals
- CVD Metal nitrides \rightarrow ALD
- PVD Metals

II - New Materials & Unit Processes:

- MIM Caps & High-k / Metal Gate
- Cu barriers
- Multipatterning

III - 3D Devices:

 \checkmark DRAM, FinFET, 3DNAND \rightarrow More ALD



Leading Logic Fully loaded

I5 ALD passes at 14nm and more than 30 at 7 nm according to estimations

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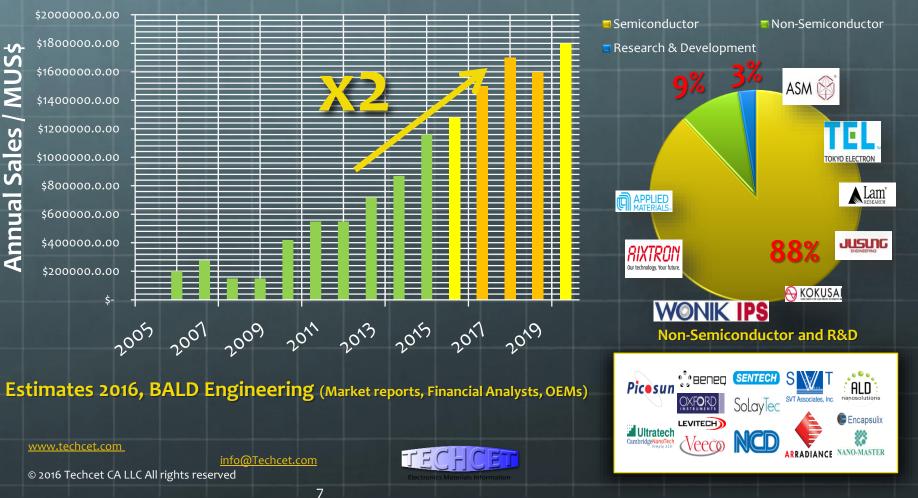
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ALD Equipment Market

ALD Wafer Systems Sales (Gartner, VLSI, ASMI)

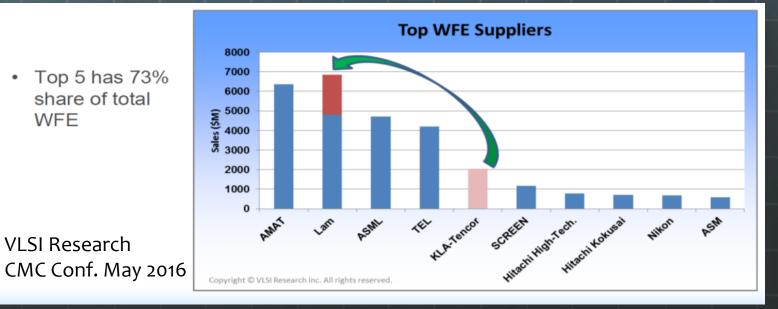
ALD Equipment 2015 US\$ 1.1 to 1.3 B



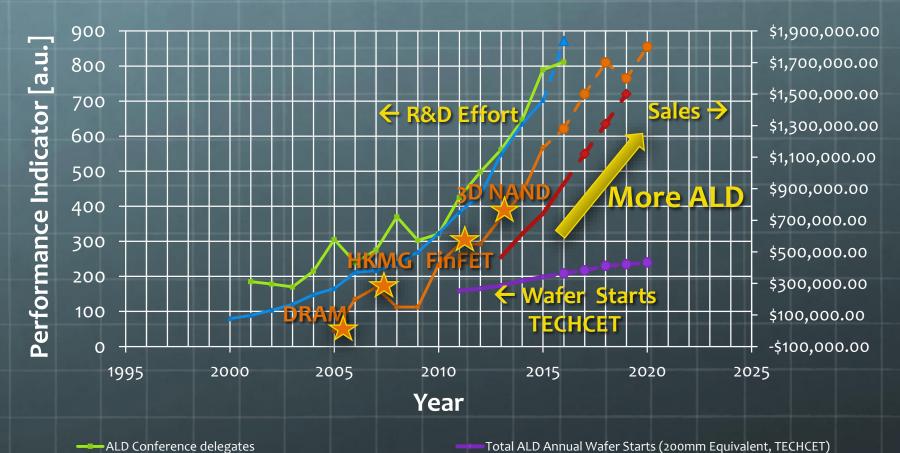
OEM Mergers

The Lam Research & KLA Merger increases concentration

However ALD Innovation drive by smaller Companies (ASM, Jusung, Ultratech, Veeco, Picosun, Beneq)



ALD Forecast



ALD Google Scholar x100

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ALD Single Wafer System Sales (Gartner, VLSI, ASMI)

ALD / CVD Precursor Forecast

Forecats Adjustment made with respect to:

- High-k consumption rate for DRAM 1,5X
- Wafer starts

ALD Distribution

Memory and patterning films drive demand





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ALD / CVD Precursor Forecast

Total ALD&Metal Precursor Market





Tungsten / WF6 Update

- Lam Research Enables Next-Generation Memory with Industry's First ALD Process for Low-Fluorine Tungsten Fill
- Uses Hydrogen down stream treatment
- Targeting 3D NAND Tungsten metallization
 - lowers fluorine content by up to 100x
 - lowers stress by up to 10x
 - reduces resistivity by over 30%





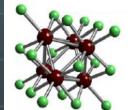
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Tungsten / WF6 Update

- WF6 is used in Tungsten metallization in CMOS, DRAM and 3DNAND – Fluorine is diffusing into the device causing derterminal reliability issues. Alternatives are:
 - WF6 process w/ H₂ treatment (see Lam Research)
 - MO-precursor \rightarrow High resistivity 8
 - Entegris 6 kg WCl6 ProEvap[™] Vessel launched 8

delivery

system



Fluorine-free tungsten



Wafergard III Pro-E Vap in-line gas filter



Flow monitor (in development)











Harvard University initiates ALD patent infringement suits towards US chip makers

- Harvard University initiates patent infringement suits to protect inventors' rights in atomic layer deposition alkyl amide precursor used for High-k applications like DRAM and other high aspect ratio capacitor based technologies.
- **US chip makers Micron & Globalfoundries are named**
- Hf & Zr metal alkyl amides are used for HfO2 and ZrO2 based high-k dielectrics in DRAM and embedded DRAM
- Logic Gate Stack does <u>not use alkyl amides</u>

Air Products Spin Off Update



September 01, 2016 Lehigh Valley, Pa. Versum Materials, Inc., the planned Electronic Materials Division spin-off company from Air Products today announced the proposed members of its Board of Directors.

About Versum Materials

With \$1 billion in sales in fiscal 2015, Versum Materials has approximately 1,900 employees, 14 manufacturing and six research and development facilities in the Americas and Asia. Versum Materials is comprised of two primary business segments, Materials (74% of fiscal 2015 revenues) and Delivery Systems and Services (26% of fiscal 2015 revenues). It participates in six of seven key semiconductor process steps, supplying high purity specialty process gas, cleaners and etchants, slurries, organosilanes and organometallics deposition films, and equipment.

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Mergers: Linde & Praxair



Praxair, Linde said to be discussing \$60 billion merger (8/19/2016) Praxair Inc. is in discussions to combine with Germany's Linde AG.

1) There is a lot of overlap between the two companies
2) Both Linde and Praxair have discontinued ALD / CVD Precursor businesses from the past -> No short term impact for ALD/CVD

Mergers: Dow/DuPont

Mergers: Commission opens indepth investigation into proposed merger between Dow and DuPont

(8/15/2016) by CMCFabsftp -Brussels, 11 August 2016 The European Union's antitrust authority opened a full-blown investigation into the proposed merger of Dow Chemical Co. and DuPont Co., which could require the companies to make bigger concessions to clear their blockbuster deal. The European Commission has opened an indepth probe to assess whether the proposed merger of Dow and [...]

The Merger would create the world's largest integrated crop protection and seeds company.

- Dow has exited all ALD Precursor business except for TMA
- Metal alkyl amide license deal with Harvard university handed over to STREM Chemicals (see Harvard lawsuit next)

"The livelihood of farmers depends on access to seeds and crop protection at competitive prices. We need to make sure that the proposed merger does not lead to higher prices or less innovation for these products."

Dow TMA Incident

OSHA Cites Dow Subsidiary Following January Explosion

(8/12/2016) by CMCFabsftp - Federal labor officials last week cited a Dow Chemical subsidiary over violations found in the wake of an explosion early this year. The Occupational Safety and Health Administration conducted an inspection of Rohm-Haas Electronics Material's North Andover, Mass., facility following the Jan. 7 explosion that injured four workers. The workers were purging cylinders of residual [...]

OSHA Cites Massachusetts Firm for Chemical Explosion

A Massachusetts chemicals manufacturer has been cited by federal labor officials following a January explosion that injured four workers. The U.S. Department of Labor says an investigation by the Occupational Safety and Health Administration determined that Rohm-Haas Electronics Material failed to adequately design, inspect, maintain and operate the chemical process that led to the fire [...]

"In total, the agency levied 11 workplace safety violations against the company and proposed \$129,200 in penalties. OSHA will also place Rohm-Haas in its Severe Violators Enforcement Program."

Thank You! JSundqvist@Techcet.com





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